SILICON (Si) POWER MOSFET A CEU02N6G



CEU02N6G

600V 🛦 3.8Ω 🛦 2A 🛦 Si MOSFET

SILICON Si MOSFET ▲ SMD type N-channel enhancement mode UL94V-0 rated flame retardant epoxy TO252 (DPAK) package ▲ MSL 3 Super high dense cell density for extremely low R_{DS(ON)} High power and current handling capability

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RoHS

REACH

MAXIMUM RATINGS

Parameter (T _c = 25°C, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V _{DS}	600V
Gate-Source Voltage	V _{GS}	±30V
Continuous Drain Current at T _c = 25°C	Ι _D	2A
Continuous Drain Current at T _c = 100°C	Ι _D	1.3A
Pulsed Drain Current Note 1	I _{DM}	8A
Maximum Power Dissipation at T _c = 25°C	PD	52W
Power Dissipation Derating above 25°C	ΔP _D	0.4W/°C
Single Pulsed Avalanche Energy Note 5	E _{AS}	11.25mJ
Single Pulsed Avalanche Current Note 5	I _{AS}	1.5A
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +150°C

THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R _{TH_JC}	2.4°C/W
Thermal Resistance, Junction-to-Ambient	R _{th_ja}	50°C/W

APPLICATIONS



PIN DESCRIPTION

Circuit Diagram	Outline - Bottom View	Pin No.	Description
D (1)		1	Drain
G (3)		2	Source
S (2)		3	Gate

CEU02N6G ▲ Rev.001 ▲ Date: 30/09/2022 ▲ Page: 1

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ELECTRICAL CHARACTERISTICS A T_c = 25°C, unless otherwise noted

ltem	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$, $I_D = 250\mu A$	BV _{DSS}	600			V
Zero Gate Voltage Drain Current	V_{DS} = 600V, V_{GS} = 0V	I _{DSS}			25	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 30V, V_{DS} = 0V$	I _{GSSF}			100	nA
Gate Body Leakage Current, Reverse	V_{GS} = -30V, V_{DS} = 0V	I _{GSSR}			-100	nA
On Characteristics Note 2						
Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250 \mu A$	V _{GS(th)}	2		4	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_{D} = 1A$	R _{DS(ON)}		3.8	5	Ω
Dynamic Characteristics Note 3						
Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	CISS		295		рF
Output Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	Coss		75		рF
Reverse Transfer Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	C _{RSS}		20		рF
Switching Characteristics Note 3						
Turn-On Delay Time	V_{DD} = 300V, V_{GS} = 10V, I_{D} = 1A, $R_{\text{G(ext)}}$ = 18 Ω	t _{D(ON)}		19	38	ns
Turn-On Rise Time	V_{DD} = 300V, V_{GS} = 10V, I_{D} = 1A, $R_{\text{G(ext)}}$ = 18 Ω	t _R		11	22	ns
Turn-Off Delay Time	V_{DD} = 300V, V_{GS} = 10V, I_{D} = 1A, $R_{\text{G(ext)}}$ = 18 Ω	t _{D(OFF)}		29	58	ns
Turn-Off Fall Time	V_{DD} = 300V, V_{GS} = 10V, I_{D} = 1A, $R_{\text{G(ext)}}$ = 18 Ω	t _F		10	20	ns
Total Gate Charge	V_{DD} = 480V, V_{GS} = 10V, I_{D} = 1A	Q _G		6.7	8.9	nC
Gate Source Charge	V_{DD} = 480V, V_{GS} = 10V, I_D = 1A	Q _{GS}		1.5		nC
Gate Drain Charge	V_{DD} = 480V, V_{GS} = 10V, I_{D} = 1A	\mathbf{Q}_{GD}		3		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current		I _S			1.9	A
Drain-Source Diode Forward Voltage Note 2	$V_{GS} = 0V$, $I_S = 1A$	V_{SD}			1.5	V

Notes

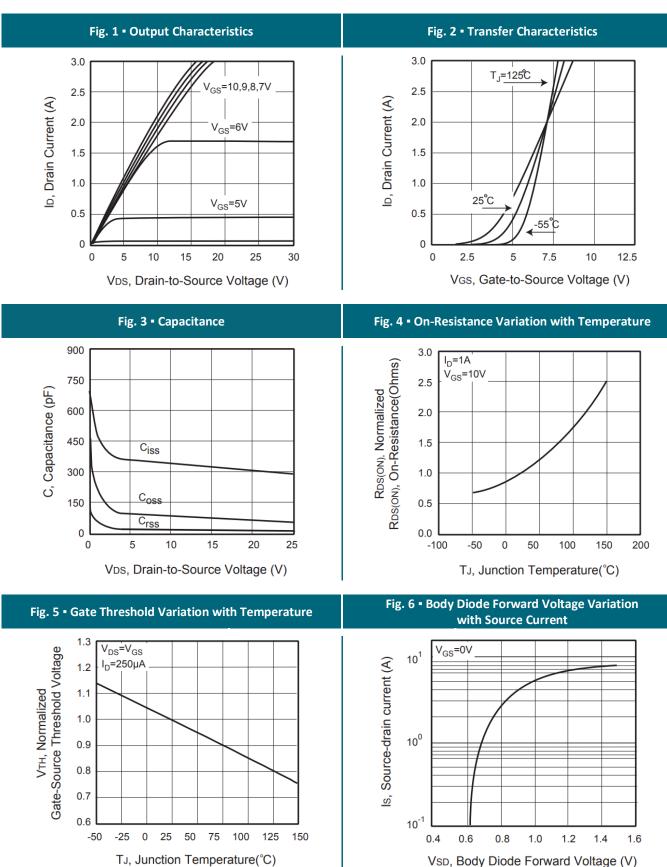
- 1: Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2: Surface Mounted on FR4 Board, t < 10 sec.
- 3: Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4: Guaranteed by design, not subject to production testing.
- 5: L = 10mH, I_{AS} = 1.5A, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25°C



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REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE



CEU02N6G ▲ Rev.001 ▲ Date: 30/09/2022 ▲ Page: 3

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REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE

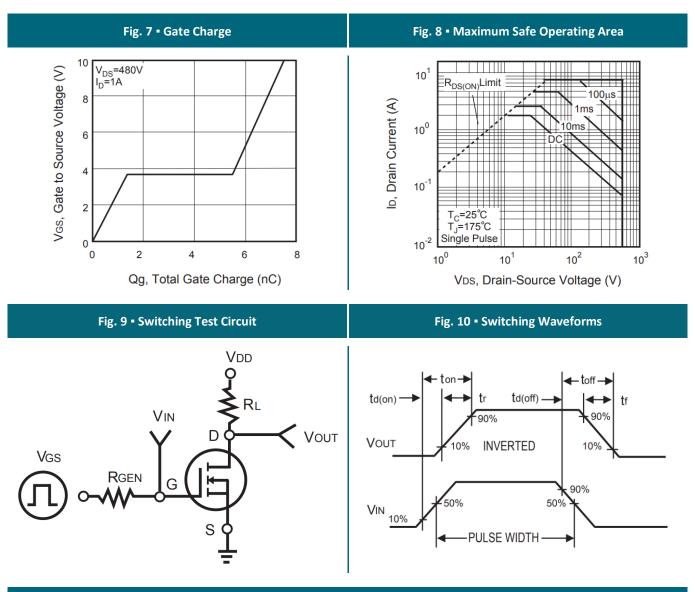
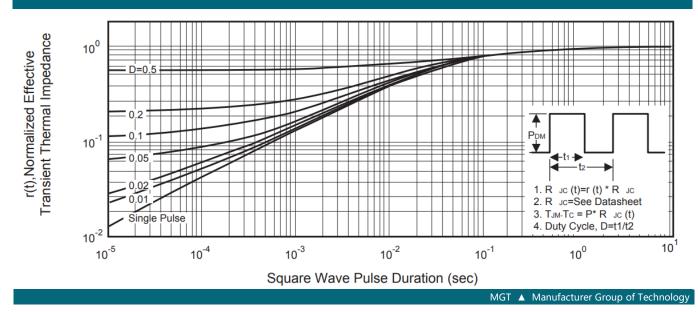


Fig. 11 • Normalized Thermal Transient Impedance Curve



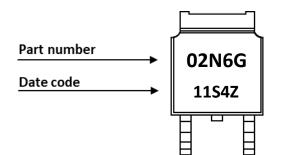
CEU02N6G ▲ Rev.001 ▲ Date: 30/09/2022 ▲ Page: 4

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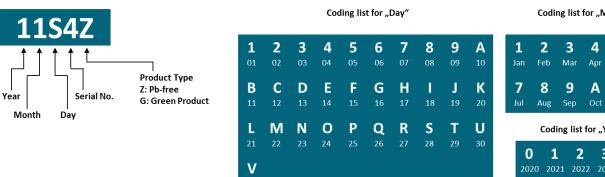






DATE CODE

Example: 11S4Z



Coding list for "Month"

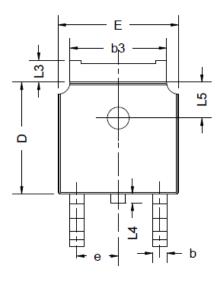
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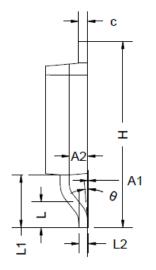


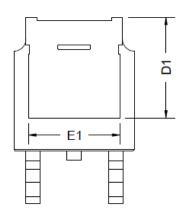


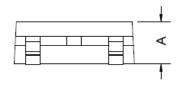
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PACKAGE OUTLINE









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	2.20	2.30	2.38	е		2.286 BSC	
A1	0.00	-	0.20	Н	9.40	10.10	10.50
A2	0.90	1.07	1.17	L	1.38	1.50	1.75
b	0.68	0.78	0.90	L1		2.90 REF	
b3	5.23	5.33	5.46	L2		0.51 BSC	
с	0.43	0.53	0.61	L3	0.88	-	1.28
D	5.98	6.10	6.22	L4	0.50		1.00
D1		5.30 REF		L5	1.65	1.80	1.95
E	6.40	6.60	6.73	θ	0°	-	8°
E1	4.63	-	-				

ORDERING INFORMATION

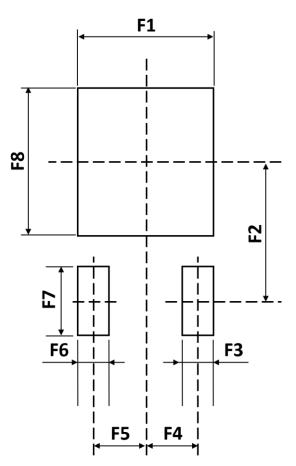
Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEU02N6G	TO252 (DPAK)	Reel	2,500pcs	5,000pcs	40,000pcs

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RECOMMENDED PAD LAYOUT



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	6.00	-	F5	-	2.29	-
F2	-	6.25	-	F6	-	1.40	-
F3	-	1.40	-	F7	-	3.00	-
F4	-	2.29	-	F8	-	6.50	-

Notes:

1. The suggested land pattern dimensions have been provided for reference only.

2. For further information, please reference document IPC-7351A.

CEU02N6G A Rev.001 A Date: 30/09/2022 A Page: 7

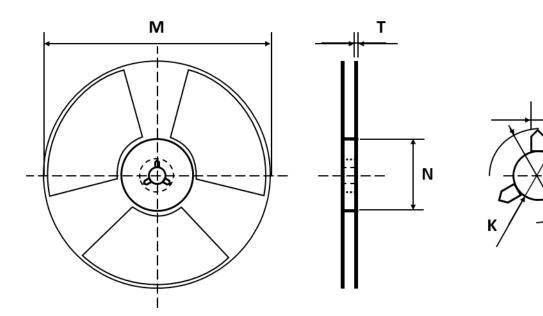


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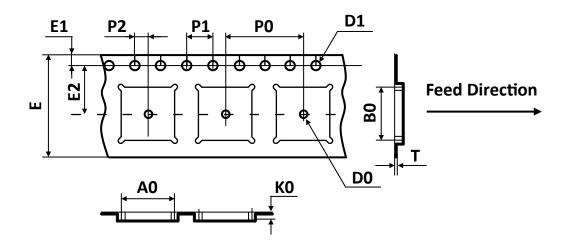


REEL DIMENSIONS All dimensions in mm



Tape Size	Reel Size	М	N	т	Н	К	S
		Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
16mm	Ø330	±2.00	±0.50	±0.20	±0.50	+0.50 -0.20	+0.50 -0.20

TAPE DIMENSIONS All dimensions in mm



Package	A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	Т
TO252	6.90	10.50	2.70	1.50	1.50	16.00	1.75	7.50	8.00	4.00	2.00	0.30
(DPAK)	±0.10	±0.10	±0.10	MIN	±0.10	+0.30 -0.20	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05

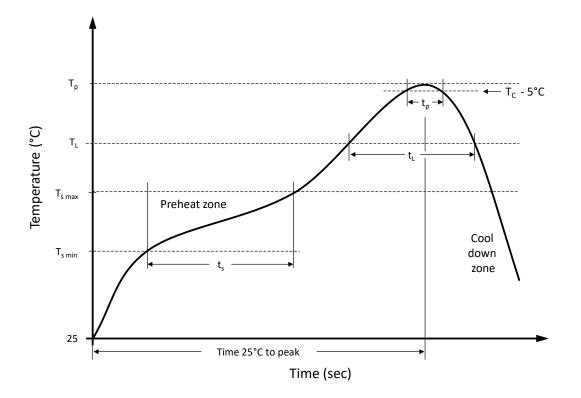


CEU02N6G ▲ Rev.001 ▲ Date: 30/09/2022 ▲ Page: 8





RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	T_{smin}	100 °C	150 °C
Preheat temperature max.	$T_{s max}$	150 °C	200 °C
Preheat time t_s from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T _L to T _p)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	ΤL	183 °C	217 °C
Time t_L maintained above T_L	t∟	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	tp	20 seconds max.	30 seconds max.
Ramp-down rate (T_L to T_p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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